

# 20V N-Channel MOSFET



SOP-8



#### Pin Definition:

1. Source	8. Drain
2. Source	7. Drain
3. Source	<ol><li>Drain</li></ol>
4. Gate	<ol><li>Drain</li></ol>

### **Key Parameter Performance**

Parameter	Value	Unit
$V_{DS}$	20	V
R <sub>DS(on)</sub> (max)	30	m
$Q_g$	11.2	nC

### **Features**

Advance Trench Process Technology High Density Cell Design for Ultra Low On-resistance

### **Application**

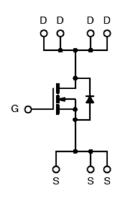
Specially Designed for Li-on Battery Packs Battery Switch Application

#### **Ordering Information**

Part No.	Package	Packing
TSM4424CS RL	SOP-8	2.5Kpcs / 13+Reel
TSM4424CS RLG	SOP-8	2.5Kpcs / 13+Reel
TSM4424CS RVG	SOP-8	3Kpcs / 13+Reel

Note: %⊕+denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

### **Block Diagram**



N-Channel MOSFET

### **Absolute Maximum Ratings** (T<sub>C</sub> = 25°C, unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	20	V	
Gate-Source Voltage		$V_{GS}$	±8	V	
Continuous Drain Current		I <sub>D</sub>	8	А	
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	30	А	
Continuous Source Current (Diode Conduction)		Is	2.2	А	
Maximum Power Dissipation	Ta = 25°C		2.5	W	
	Ta = 75°C	P <sub>D</sub>	1.3		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance Junction to Foot	R <sub>JF</sub>	25	°C/W
Thermal Resistance Junction to Ambient	R <sub>JA</sub>	52.5	°C/W



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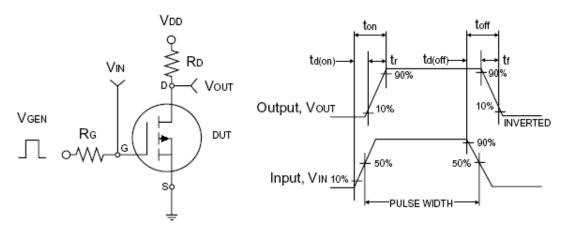


**Electrical Specifications** 

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static <sup>(Note 2)</sup>		<b>'</b>		•		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	1	0.65	1	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I <sub>GSS</sub>	1		±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I <sub>DSS</sub>	1		1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I <sub>D(ON)</sub>	30			Α
	$V_{GS} = 4.5V, I_D = 4.5A$			23	30	m
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 3.5A$	R <sub>DS(ON)</sub>	1	25	35	
	$V_{GS} = 1.8V, I_D = 2.0A$		1	35	45	
Forward Transconductance	$V_{DS} = 10V, I_D = 6A$	<b>g</b> fs	1	40		S
Diode Forward Voltage	$I_S = 1.7A$ , $V_{GS} = 0V$	$V_{SD}$	1	0.8	1.2	V
Dynamic <sup>(Note 3)</sup>						
Total Gate Charge	$V_{DS} = 10V, I_D = 4.5A,$ $V_{GS} = 4.5V$	$Q_g$	1	11.2	14	
Gate-Source Charge		$Q_gs$	-	1.4		nC
Gate-Drain Charge		$Q_gd$	-	2.2		
Input Capacitance	.,	C <sub>iss</sub>	-	500		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	$C_{oss}$	-	300		pF
Reverse Transfer Capacitance		$C_{rss}$	1	140		
Switching <sup>(Note 4)</sup>						
Turn-On Delay Time	$V_{DD} = 10V, R_L = 10$ , $I_D = 1A, V_{GEN} = 4.5V,$ $R_G = 6$	t <sub>d(on)</sub>		15	25	
Turn-On Rise Time		t <sub>r</sub>		30	60	no
Turn-Off Delay Time		t <sub>d(off)</sub>		35	70	ns
Turn-Off Fall Time		t <sub>f</sub>	1	15	45	

#### Notes:

- 1. Pulse width limited by the maximum junction temperature
- 2. Pulse test: PW m300µs, duty cycle m2%
- 3. For DESIGN AID ONLY, not subject to production testing.
- 4. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

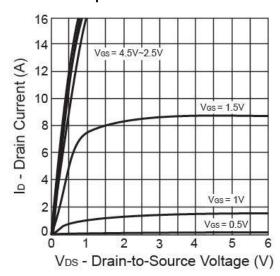


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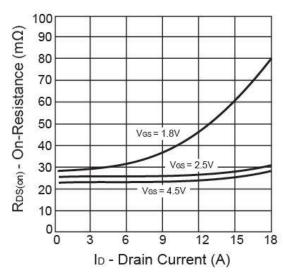


#### **Electrical Characteristics Curve**

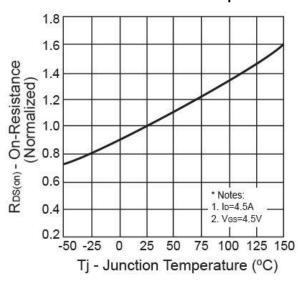
#### **Output Characteristics**



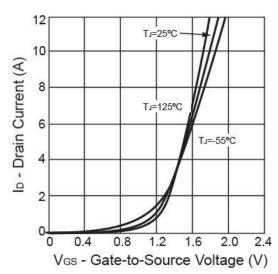
#### On-Resistance vs. Drain Current



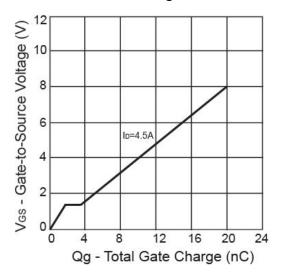
On-Resistance vs. Junction Temperature



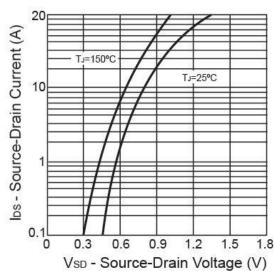
#### **Transfer Characteristics**



**Gate Charge** 



Source-Drain Diode Forward Voltage



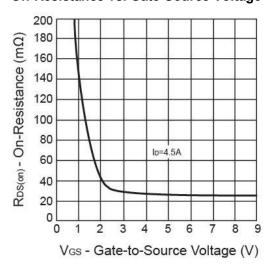


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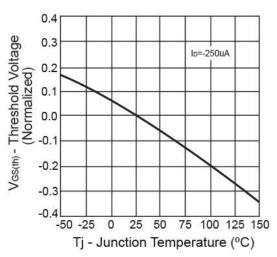


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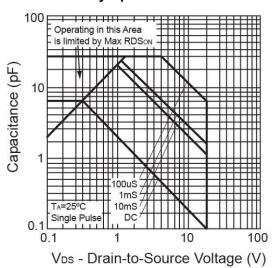
#### On-Resistance vs. Gate-Source Voltage



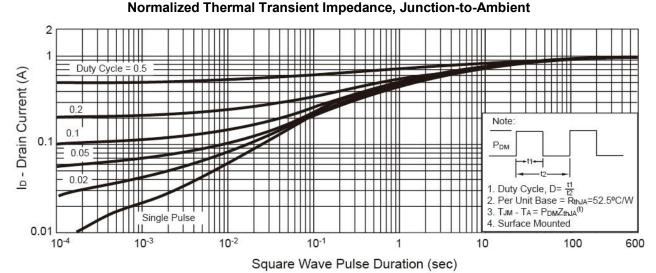
#### **Threshold Voltage**



#### **Safety Operation Area**



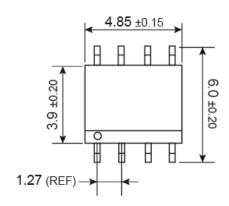
#### N 1 17 17 17 17 1 1 1 1 1 1

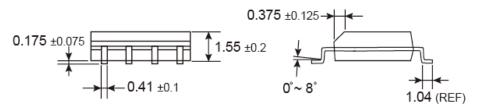






# **SOP-8 Mechanical Drawing**

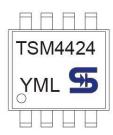




5/6

**Unit: Millimeters** 

## **Marking Diagram**



Y = Year Code

**M** = Month Code

(**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apl, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug, **I**=Sep, **J**=Oct, **K**=Nov, **L**=Dec)

Month Code for Halogen Free Product
(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

L = Lot Code

Version: C14



# TSM4424 20V N-Channel MOSFET

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